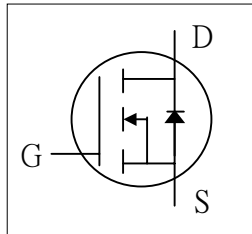




- ▼ 100% Avalanche Test
- ▼ Fast Switching
- ▼ Simple Drive Requirement

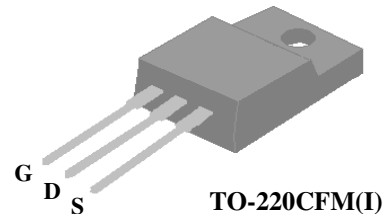


| | |
|--------------|---------------|
| BV_{DSS} | 650V |
| $R_{DS(ON)}$ | 0.75 Ω |
| I_D | 9A |

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220CFM isolation package is widely preferred for all commercial-industrial through hole applications.



Absolute Maximum Ratings

| Symbol | Parameter | Rating | Units |
|-----------------------|--|------------|---------------|
| V_{DS} | Drain-Source Voltage | 650 | V |
| V_{GS} | Gate-Source Voltage | +30 | V |
| $I_D@T_C=25^\circ C$ | Continuous Drain Current, V_{GS} @ 10V | 9 | A |
| $I_D@T_C=100^\circ C$ | Continuous Drain Current, V_{GS} @ 10V | 5 | A |
| I_{DM} | Pulsed Drain Current ¹ | 40 | A |
| $P_D@T_C=25^\circ C$ | Total Power Dissipation | 42 | W |
| | Linear Derating Factor | 0.34 | W/ $^\circ C$ |
| E_{AS} | Single Pulse Avalanche Energy ² | 40.5 | mJ |
| I_{AR} | Avalanche Current | 9 | A |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ C$ |
| T_J | Operating Junction Temperature Range | -55 to 150 | $^\circ C$ |

Thermal Data

| Symbol | Parameter | Value | Units |
|--------|--|-------|--------------|
| Rthj-c | Maximum Thermal Resistance, Junction-case | 3 | $^\circ C/W$ |
| Rthj-a | Maximum Thermal Resistance, Junction-ambient | 65 | $^\circ C/W$ |



Electrical Characteristics@T_J=25°C(unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|-------------------------------------|--|--|------|------|------|-------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =1mA | 650 | - | - | V |
| ΔBV _{DSS} /ΔT _J | Breakdown Voltage Temperature Coefficient | Reference to 25°C, I _D =1mA | - | 0.6 | - | V/°C |
| R _{DS(ON)} | Static Drain-Source On-Resistance ³ | V _{GS} =10V, I _D =4.5A | - | - | 0.75 | Ω |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250uA | 2 | - | 4 | V |
| g _{fs} | Forward Transconductance | V _{DS} =50V, I _D =4.5A | - | 4.5 | - | S |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =600V, V _{GS} =0V | - | - | 10 | uA |
| | Drain-Source Leakage Current (T _J =125°C) | V _{DS} =480V, V _{GS} =0V | - | - | 500 | uA |
| I _{GSS} | Gate-Source Leakage | V _{GS} =±30V, V _{DS} =0V | - | - | +100 | nA |
| Q _g | Total Gate Charge ³ | I _D =9A | - | 44 | - | nC |
| Q _{gs} | Gate-Source Charge | V _{DS} =480V | - | 11 | - | nC |
| Q _{gd} | Gate-Drain ("Miller") Charge | V _{GS} =10V | - | 12 | - | nC |
| t _{d(on)} | Turn-on Delay Time ³ | V _{DD} =300V | - | 19 | - | ns |
| t _r | Rise Time | I _D =9A | - | 21 | - | ns |
| t _{d(off)} | Turn-off Delay Time | R _G =10Ω, V _{GS} =10V | - | 56 | - | ns |
| t _f | Fall Time | R _D =34Ω | - | 24 | - | ns |
| C _{iss} | Input Capacitance | V _{GS} =0V | - | 2660 | - | pF |
| C _{oss} | Output Capacitance | V _{DS} =25V | - | 170 | - | pF |
| C _{rss} | Reverse Transfer Capacitance | f=1.0MHz | - | 10 | - | pF |

Source-Drain Diode

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|-----------------|---|---|------|------|------|-------|
| I _S | Continuous Source Current (Body Diode) | V _D =V _G =0V , V _S =1.5V | - | - | 9 | A |
| I _{SM} | Pulsed Source Current (Body Diode) ¹ | | - | - | 40 | A |
| V _{SD} | Forward On Voltage ³ | T _J =25°C, I _S =9A, V _{GS} =0V | - | - | 1.5 | V |

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Starting T_J=25°C , V_{DD}=50V , L=1mH , R_G=25Ω , I_{AS}=9A.
- 3.Pulse test

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

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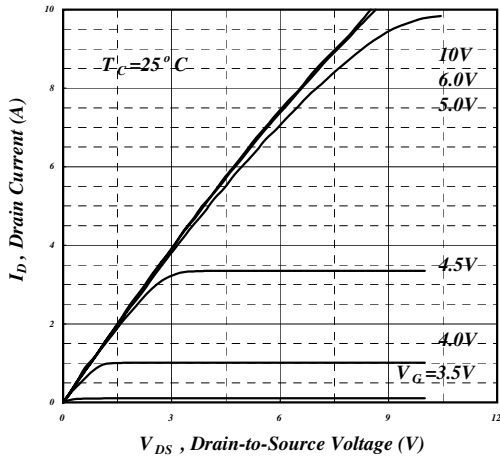


Fig 1. Typical Output Characteristics

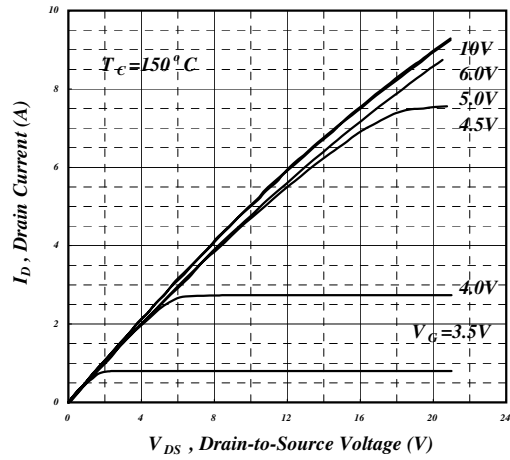


Fig 2. Typical Output Characteristics

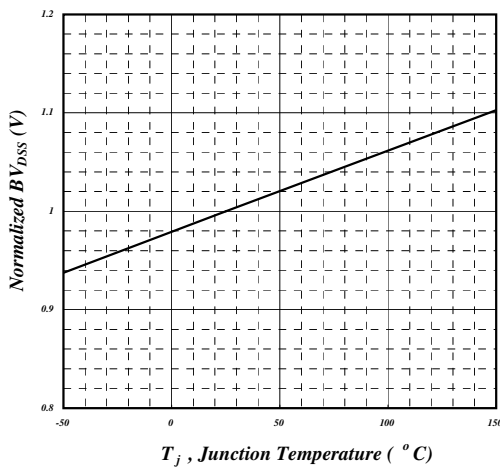


Fig 3. Normalized BV_{DSS} v.s. Junction Temperature

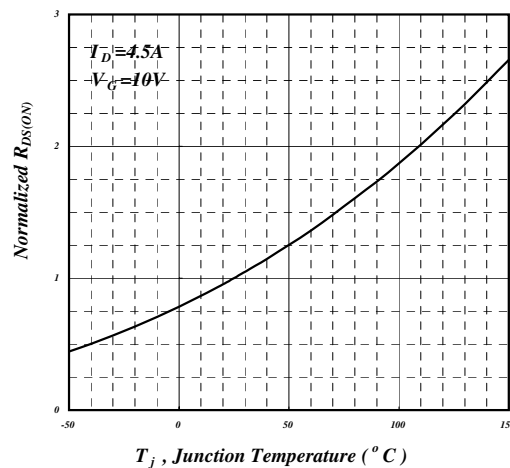


Fig 4. Normalized On-Resistance v.s. Junction Temperature

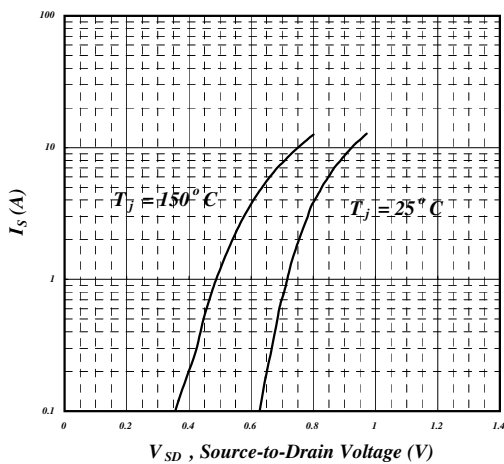


Fig 5. Forward Characteristic of Reverse Diode

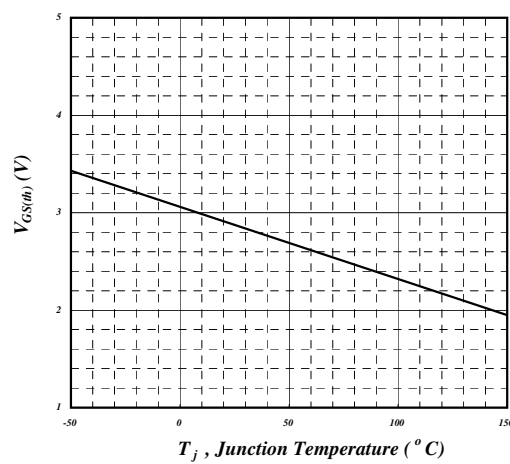


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

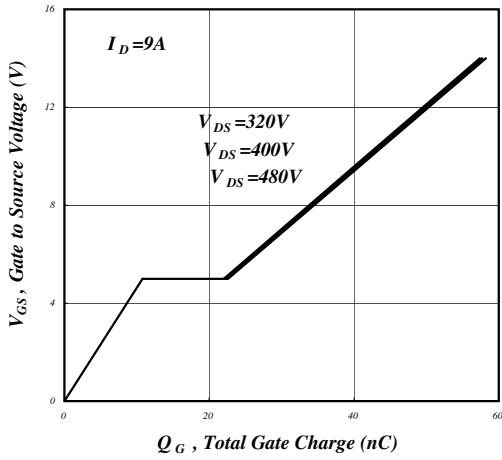


Fig 7. Gate Charge Characteristics

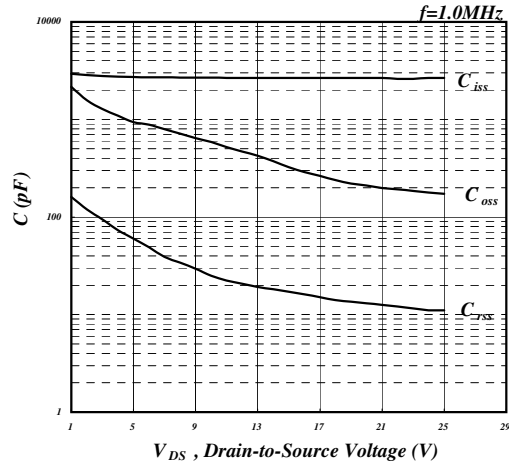


Fig 8. Typical Capacitance Characteristics

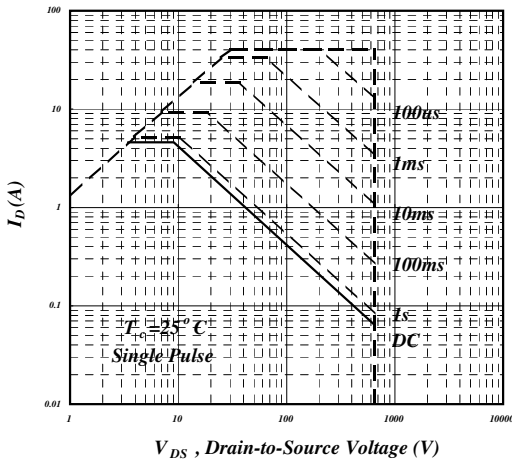


Fig 9. Maximum Safe Operating Area

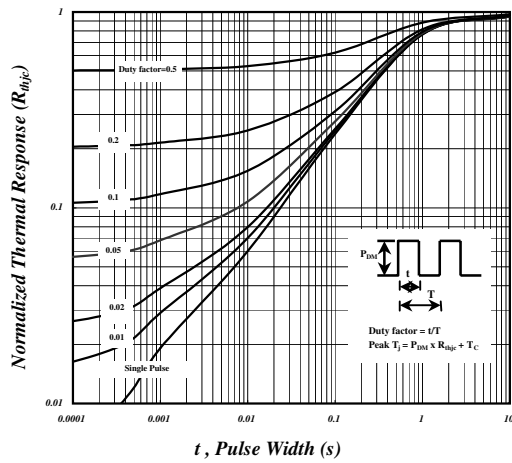


Fig 10. Effective Transient Thermal Impedance

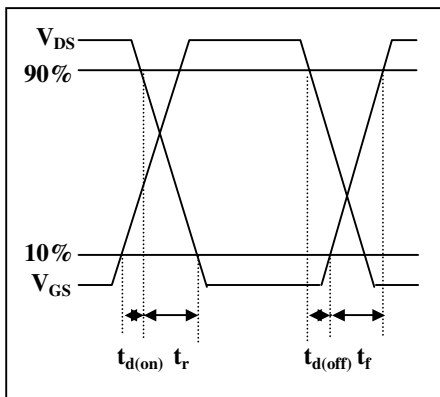


Fig 11. Switching Time Waveform

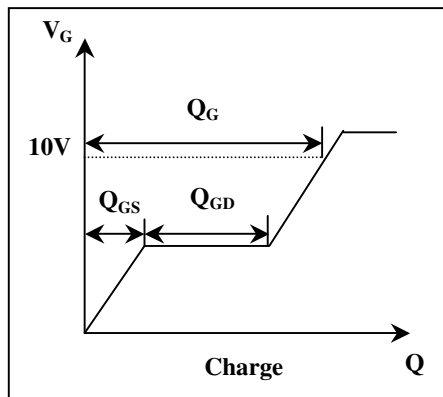


Fig 12. Gate Charge Waveform